

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP12T13A uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =120V,I_D =135A
 R_{DS(ON)} <4.6mΩ @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

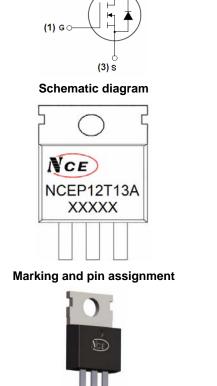
100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP12T13A	NCEP12T13A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	120	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	135	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	102	А
Pulsed Drain Current	I _{DM}	500	А
Maximum Power Dissipation	PD	210	W
Derating factor		1.4	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1050	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C
Thermal Characteristic	·	•	
Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	0.71	°C/W



TO-220-3L top view

(2) D



Electrical Characteristics (T_c=25 $^\circ\!\mathrm{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	i					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	120		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =120V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·		•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.3	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =65A	-	4.1	4.6	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =65A	-	60	-	S
Dynamic Characteristics (Note4)	· ·					
Input Capacitance	C _{lss}	<u>)</u> () () () () () () () () () () () () ()	-	6394	-	PF
Output Capacitance	C _{oss}	V _{DS} =60V,V _{GS} =0V, F=1.0MHz	-	510	-	PF
Reverse Transfer Capacitance	C _{rss}		-	27	-	PF
Switching Characteristics (Note 4)	· · · ·					
Turn-on Delay Time	t _{d(on)}		-	18	-	nS
Turn-on Rise Time	tr	V _{DD} =60V,I _D =65A V _{GS} =10V,R _G =4.7Ω	-	75	-	nS
Turn-Off Delay Time	t _{d(off)}		-	47	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Qg		-	85.8		nC
Gate-Source Charge	Q _{gs}	V_{DS} =60V,I _D =65A,	-	38		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	13.9		nC
Drain-Source Diode Characteristics	· ·		•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =135A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	135	А
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	63		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	142		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

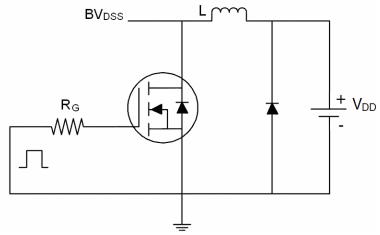
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ \!\! C$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25\Omega

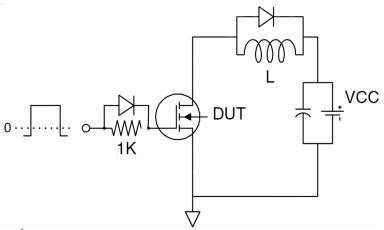


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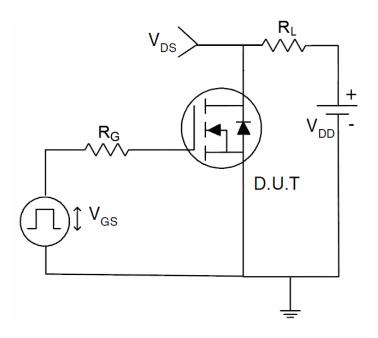
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit

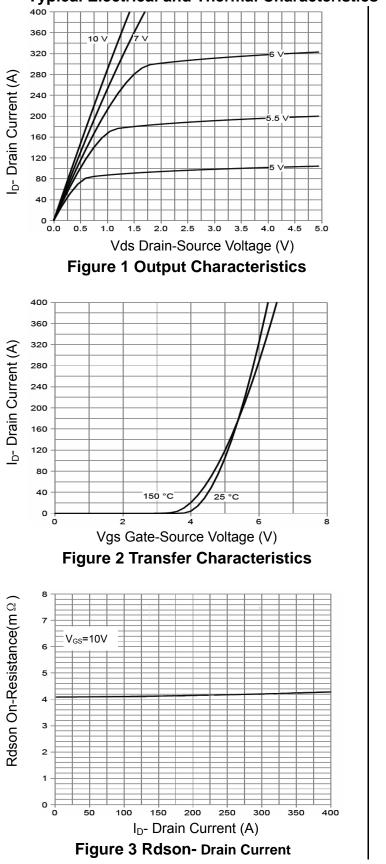


3) Switch Time Test Circuit









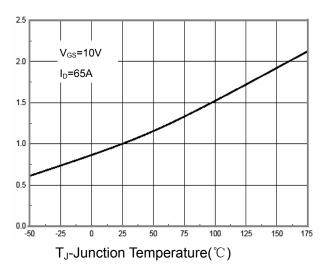
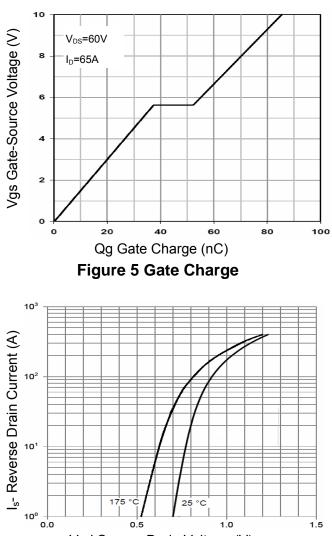


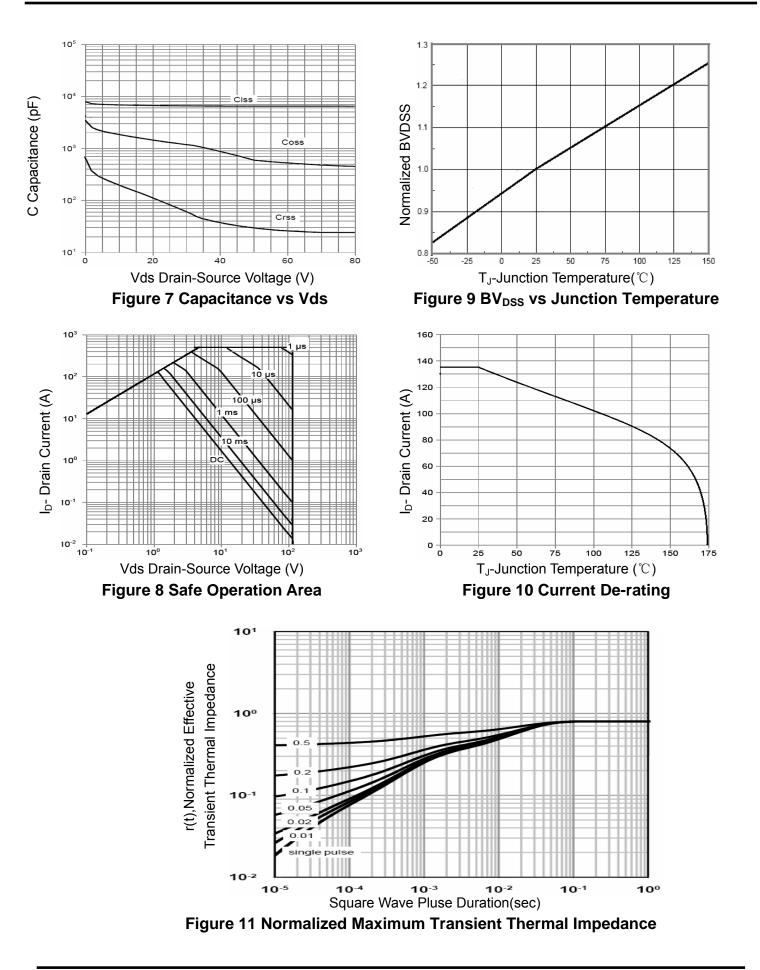
Figure 4 Rdson-JunctionTemperature



Vsd Source-Drain Voltage (V) Figure 6 Source- Drain Diode Forward

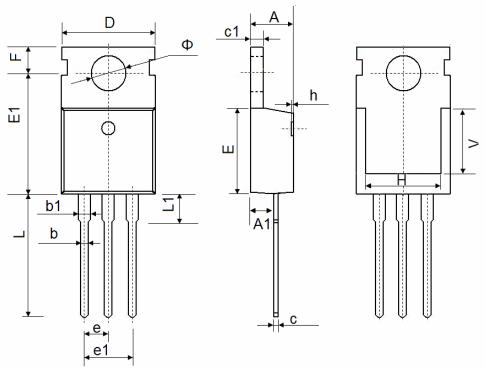


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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	



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